

# **Test Report**

美麗微半導體股份有限公司 FORMOSA MICROSEMI CO., LTD. 新北市土城區中央路三段208號5樓

5F., NO. 208, SEC. 3, ZHONGYANG RD., TUCHENG DIST., NEW TAIPEI CITY 23680, TAIWAN

以下測試樣品係由申請廠商所提供及確認 (The following sample(s) was/were submitted and identified by/on behalf of the applicant as):

號碼(No.): CE/2015/93571B 日期(Date): 2015/09/24

送樣廠商(Sample Submitted By)

美麗微半導體股份有限公司 (FORMOSA MICROSEMI CO., LTD.)

樣品名稱(Sample Description)

LEADED PLASTIC MOLDED PRODUCTS (各項軸式塑封產品)

樣品型號(Style/Item No.)

R-1 / A-405 / D0-41/ D0-15 / R-3 / D0-201AD / D0-201AE / R-6 / P600 /

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FV5M / FV5M-1 / FV5M-2 / FH / HV03

收件日期(Sample Receiving Date)

2015/09/01 AND 2015/09/15

測試期間(Testing Period)

2015/09/01 TO 2015/09/07 AND 2015/09/15 TO 2015/09/21

請見下一頁 (Please refer to next pages). 測試結果(Test Results) :

> \* 此份報告為合併CE/2015/90390及CE/2015/93571之報告 \* (This report is combined with reports of CE/2015/90390 and CE/2015/93571)



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測試結果(Test Results)

測試部位(PART NAME)No.1 銀色金屬腳鍍層 (PLATING LAYER OF SILVER COLORED METAL PIN (CE/2015/90390

No. 1))

測試部位(PART NAME)No. 2 銀色金屬腳鍍層 (PLATING LAYER OF SILVER COLORED METAL PIN (CE/2015/93571)) 測試部位(PART NAME)No.3 銀色金屬腳底材 (BASE MATERIAL OF SILVER COLORED METAL PIN (CE/2015/90390

No. 2)

測試部位(PART NAME)No. 4 本體混測 (MIXED ALL PARTS OF BODY (CE/2015/90390 No. 3))

測試項目 (Test Items)	單位 (Unit)	· ·	方法偵測 極限値 (MDL)	結果(Result)		
(lest Items)	(UIII L)			No. 1	No. 2	No. 3
鎬 / Cadmium (Cd)	mg/kg	酸洗脫鍍層,參考IEC 62321-5: 2013方法,以感應耦合電漿原子發射光譜儀檢測. / IEC 62321-5: 2013 application of modified digestion by surface etching and performed by ICP-AES.	2	n. d.		
	mg/kg	参考IEC 62321-5: 2013方法,以 感應耦合電漿原子發射光譜儀檢 測. / With reference to IEC 62321-5: 2013 and performed by ICP-AES.	2			n. d.
鉛 / Lead (Pb)	mg/kg	酸洗脫鍍層,參考IEC 62321-5: 2013方法,以感應耦合電漿原子發射光譜儀檢測. / IEC 62321-5: 2013 application of modified digestion by surface etching and performed by ICP-AES.	2		37. 3	
	mg/kg	参考IEC 62321-5: 2013方法,以 感應耦合電漿原子發射光譜儀檢 測. / With reference to IEC 62321-5: 2013 and performed by ICP-AES.	2			n. d.



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測試項目 (Test Items)	單位 (Unit)	測試方法	方法偵測 極限值 (MDL)	結果 (Result)		
		(Method)		No. 1	No. 2	No. 3
汞 / Mercury (Hg)	mg/kg	酸洗脫鍍層,參考IEC 62321-4: 2013方法,以感應耦合電漿原子發射光譜儀檢測. / IEC 62321-4: 2013 application of modified digestion by surface etching and performed by ICP-AES.	2	n. d.		
	mg/kg	參考IEC 62321-4: 2013方法,以 感應耦合電漿原子發射光譜儀檢 測. / With reference to IEC 62321-4: 2013 and performed by ICP-AES.	2			n. d.
六價鉻 / Hexavalent Chromium Cr(VI)	**	參考IEC 62321: 2008方法,以沸水萃取法檢測. / With reference to IEC 62321: 2008 and performed by Boiling water extraction Method.#	#	Negative		Negative
鎳 / Nickel (Ni)	mg/kg	参考US EPA 3050B方法,以感應耦合電漿原子發射光譜儀檢測./ With reference to US EPA Method 3050B. Analysis was performed by ICP-AES.	2	19. 4		
全氟辛烷磺酸 / Perfluorooctane sulfonates (PFOS-Acid, Metal Salt, Amide)	μg/m²	參考US EPA 3550C: 2007方法,以 液相層析/質譜儀檢測. / With reference to US EPA 3550C: 2007. Analysis was performed by LC/MS.	1	n. d.		
全氟辛酸 / PFOA (CAS No.: 335-67-1)	μg/m²	參考US EPA 3550C: 2007方法,以 液相層析/質譜儀檢測. / With reference to US EPA 3550C: 2007. Analysis was performed by LC/MS.	1	n. d.		

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測試項目 (Test Items)	單位 (Unit)	測試方法 (Method)	方法偵測 極限值	結果 (Result)
(165t Items)	(onit t)	(mo thou)	(MDL)	No. 4
鎘 / Cadmium (Cd)	mg/kg	參考IEC 62321-5: 2013方法,以 感應耦合電漿原子發射光譜儀檢 測. / With reference to IEC 62321-5: 2013 and performed by ICP-AES.	2	n. d.
鉛 / Lead (Pb)	mg/kg	參考IEC 62321-5: 2013方法,以 感應耦合電漿原子發射光譜儀檢 測. / With reference to IEC 62321-5: 2013 and performed by ICP-AES.	2	4380
汞 / Mercury (Hg)	mg/kg	參考IEC 62321-4: 2013方法,以 感應耦合電漿原子發射光譜儀檢 測. / With reference to IEC 62321-4: 2013 and performed by ICP-AES.	2	n. d.
六價鉻 / Hexavalent Chromium Cr(VI)	mg/kg	參考IEC 62321: 2008方法, 以UV-VIS檢測. / With reference to IEC 62321: 2008 and performed by UV-VIS.	2	n. d.
銻 / Antimony (Sb)	mg/kg	參考US EPA 3052方法,以感應耦合電漿原子發射光譜儀檢測./ With reference to US EPA Method 3052. Analysis was performed by ICP-AES.	2	n. d.
砷 / Arsenic (As)	mg/kg	參考US EPA 3052方法,以感應耦合電漿原子發射光譜儀檢測./ With reference to US EPA Method 3052. Analysis was performed by ICP-AES.	2	n. d.



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測試項目 (Test Items)	單位 (Unit)	測試方法 (Method)	方法偵測 極限値 (MDL)	結果 (Result) No.4
鄰苯二甲酸二異丁酯 / DIBP (Di-isobutyl phthalate) (CAS No.: 84-69-5)	mg/kg		50	n. d.
鄰苯二甲酸二丁酯 / DBP (Dibutyl phthalate) (CAS No.: 84-74-2)	mg/kg		50	n. d.
鄰苯二甲酸丁苯甲酯 / BBP (Butyl Benzyl phthalate) (CAS No.: 85-68-7)	mg/kg	参考IEC 62321-8 (111/321/CD),	50	n. d.
鄰苯二甲酸二 (2-乙基己基)酯 / DEHP (Di- (2-ethylhexyl) phthalate) (CAS No.: 117-81-7)	mg/kg	以氣相層析儀/質譜儀檢測之. / With reference to IEC 62321-8 (111/321/CD). Analysis was	50	n. d.
鄰苯二甲酸二正辛酯 / DNOP (Di-n-octyl phthalate) (CAS No.: 117-84-0)	mg/kg	performed by GC/MS.	50	n. d.
鄰苯二甲酸二異壬酯 / DINP (Di- isononyl phthalate) (CAS No.: 28553- 12-0; 68515-48-0)	mg/kg		50	n. d.
鄰苯二甲酸二異癸酯 / DIDP (Di- isodecyl phthalate) (CAS No.: 26761- 40-0; 68515-49-1)	mg/kg		50	n. d.
六溴環十二烷及所有主要被辨別出的異構物 / Hexabromocyclododecane (HBCDD) and all major diastereoisomers identified ( $\alpha$ – HBCDD, $\beta$ – HBCDD, $\gamma$ – HBCDD) (CAS No.: 25637–99–4 and 3194–55–6 (134237–51–7, 134237–50–6, 134237–52–8))	mg/kg	參考IEC 62321: 2008方法, 以氣相層析/質譜儀檢測. / With reference to IEC 62321: 2008 method. Analysis was performed by GC/MS.	5	n. d.



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測試項目 (Test Items)	單位 (Unit)	測試方法 (Method)	方法偵測 極限值	結果 (Result)
(Test Ttems)	(onit)	(method)	(MDL)	No. 4
多溴聯苯總和 / Sum of PBBs	mg/kg		-	n. d.
一溴聯苯 / Monobromobiphenyl	mg/kg		5	n. d.
二溴聯苯 / Dibromobiphenyl	mg/kg		5	n. d.
三溴聯苯 / Tribromobiphenyl	mg/kg		5	n. d.
四溴聯苯 / Tetrabromobiphenyl	mg/kg		5	n. d.
五溴聯苯 / Pentabromobiphenyl	mg/kg	]	5	n. d.
六溴聯苯 / Hexabromobiphenyl	mg/kg	]	5	n. d.
七溴聯苯 / Heptabromobiphenyl	mg/kg	]	5	n. d.
八溴聯苯 / Octabromobiphenyl	mg/kg		5	n. d.
九溴聯苯 / Nonabromobiphenyl	mg/kg	   参考IEC 62321-6: 2015方法,以	5	n. d.
十溴聯苯 / Decabromobiphenyl	mg/kg	氣相層析/質譜儀檢測. / With	5	n. d.
多溴聯苯醚總和 / Sum of PBDEs	mg/kg	reference to IEC 62321-6: 2015	_	n. d.
一溴聯苯醚 / Monobromodiphenyl ether	mg/kg	and performed by GC/MS.	5	n. d.
二溴聯苯醚 / Dibromodiphenyl ether	mg/kg	]	5	n. d.
三溴聯苯醚 / Tribromodiphenyl ether	mg/kg	]	5	n. d.
四溴聯苯醚 / Tetrabromodiphenyl ether	mg/kg		5	n. d.
五溴聯苯醚 / Pentabromodiphenyl ether	mg/kg		5	n. d.
六溴聯苯醚 / Hexabromodiphenyl ether	mg/kg		5	n. d.
七溴聯苯醚 / Heptabromodiphenyl ether	mg/kg		5	n. d.
八溴聯苯醚 / Octabromodiphenyl ether	mg/kg		5	n. d.
九溴聯苯醚 / Nonabromodiphenyl ether	mg/kg		5	n. d.
十溴聯苯醚 / Decabromodiphenyl ether	mg/kg		5	n. d.



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#### 備註(Note):

- 1. mg/kg = ppm; 0. 1wt% = 1000ppm
- 2. n.d. = Not Detected (未檢出)
- 3. MDL = Method Detection Limit (方法偵測極限值)
- 4. "-" = Not Regulated (無規格值)
- 5. "---" = Not Conducted (未測項目)
- 6. \*\*= Qualitative analysis (No Unit) 定性分析(無單位)
- 7. # = a. Positive means the presence of CrVI on the tested areas (Positive表示測試區域偵測到六價鉻)
  - b. Negative means the absence of CrVI on the tested areas (Negative表示測試區域未偵測到六價鉻)

The detected concentration in boiling-water-extraction solution is equal or greater than 0.02 mg/kg with 50 cm² tested areas . / 該溶液濃度≧0.02 mg/kg with 50 cm² (tested areas)

- 8. For No. 4: 樣品的測試是基於申請人要求混合測試,報告中的混合測試結果不代表其中個別單一材質的含量. (The samples was/were analyzed on behalf of the applicant as mixing sample in one testing. The above results was/were only given as the informality value.)
- 9. 依據申請公司宣稱測試部位 No.4 之測試結果為豁免,係依據歐盟指令2011/65/EU Annex II, 其產品為"高熔點銲錫 中的鉛"及"含鉛之玻璃或陶瓷的電器和電子元件,介電陶瓷電容器除外"時,"鉛"為豁免.

(The result from lead content No. 4 is exempted according to the declaration from applicant in compliance with RoHS Directive 2011/65/EU Annex II for Lead in high melting temperature type solders and Electrical and electronic components containing lead in a glass or ceramic other than dielectric ceramic in capacitors.

#### PFOS参考資訊(Reference Information): 持久性有機污染物 POPs - (EU) 757/2010

PFOS濃度在物質或製備中不得超過0.001%(10ppm),在半成品、成品或零部件中不得超過0.1%(1000ppm),在紡織品或塗 層材料中不得超過1µg/m²。

(Outlawing PFOS as substances or preparations in concentrations above 0.001% (10ppm), in semi-finished products or articles or parts at a level above 0.1%(1000ppm), in textiles or other coated materials above  $1\mu g/m^2$ .)

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美麗微半導體股份有限公司 FORMOSA MICROSEMI CO., LTD. 新北市土城區中央路三段208號5樓 5F., NO. 208, SEC. 3, ZHONGYANG RD., TUCHENG DIST., NEW TAIPEI CITY 23680, TAIWAN No. 1, No. 2

號碼(No.): CE/2015/93571B

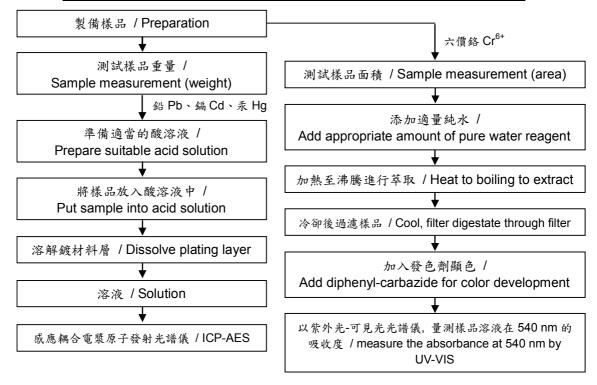
根據以下的流程圖之條件,樣品之外部鍍層已完全溶解。( 六價鉻測試方法除外) / The plating layer of samples were dissolved totally by pre-conditioning method according to below flow chart. (Cr<sup>6+</sup> test method excluded)

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- 測試人員:楊登偉 / Name of the person who made measurement: Climbgreat Yang
- 測試負責人:張啟興 / Name of the person in charge of measurement: Troy Chang

#### 鍍層重金屬測試流程圖 / Flow Chart of Stripping method for metal analysis





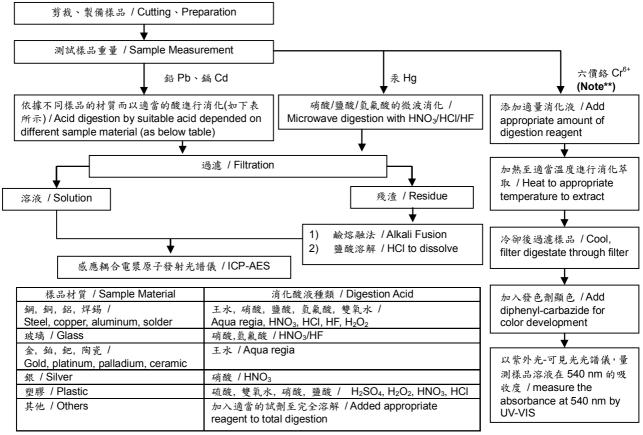
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5F., NO. 208, SEC. 3, ZHONGYANG RD., TUCHENG DIST., NEW TAIPEI CITY 23680, TAIWAN No. 3, No. 4

- 根據以下的流程圖之條件,樣品已完全溶解。(六價鉻測試方法除外) / These samples were 1) dissolved totally by pre-conditioning method according to below flow chart. (Cr<sup>6+</sup> test method excluded)
- 測試人員:楊登偉 / Name of the person who made measurement: Climbgreat Yang
- 測試負責人: 張啟興 / Name of the person in charge of measurement: Troy Chang



#### Note\*\* (For IEC 62321)

- (1) 針對非金屬材料加入鹼性消化液,加熱至 90~95℃ 萃取. / For non-metallic material, add alkaline digestion reagent and heat to 90~95℃
- (2) 針對金屬材料加入純水,加熱至沸騰萃取. / For metallic material, add pure water and heat to boiling.

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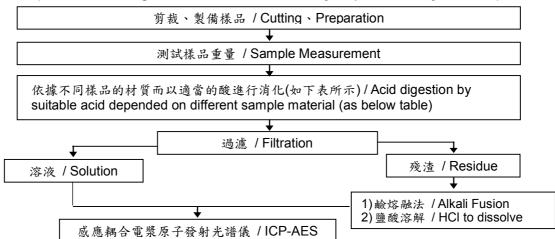
根據以下的流程圖之條件,樣品已完全溶解。 / These samples were dissolved totally by pre-conditioning method according to below flow chart.

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- 測試人員:楊登偉 / Name of the person who made measurement: Climbgreat Yang
- 測試負責人:張啟興 / Name of the person in charge of measurement: Troy Chang

#### 元素以 ICP-AES 分析的消化流程圖 (Flow Chart of digestion for the elements analysis performed by ICP-AES)



鋼,銅,鋁,焊錫 / Steel, copper, aluminum, solder	王水,硝酸,鹽酸,氫氟酸,雙氧水/
	Aqua regia, HNO <sub>3</sub> , HCl, HF, H <sub>2</sub> O <sub>2</sub>
玻璃 / Glass	硝酸,氫氟酸 / HNO <sub>3</sub> /HF
金,鉑,鈀,陶瓷 / Gold, platinum, palladium, ceramic	王水 / Aqua regia
銀 / Silver	硝酸 / HNO <sub>3</sub>
塑膠 / Plastic	硫酸,雙氧水,硝酸,鹽酸 / H <sub>2</sub> SO <sub>4</sub> , H <sub>2</sub> O <sub>2</sub> , HNO <sub>3</sub> , HCl
其他 / Others	加入適當的試劑至完全溶解 / Added appropriate reagent to total digestion



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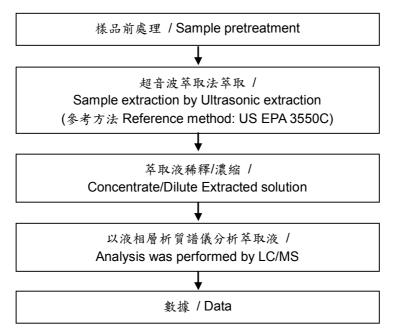
號碼(No.): CE/2015/93571B

### 全氟辛酸/全氟辛烷磺酸分析流程圖 / PFOA/PFOS analytical flow chart

日期(Date): 2015/09/24

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- 測試人員: 翁賜彬 / Name of the person who made measurement: Roman Wong
- 測試負責人:張啟興 / Name of the person in charge of measurement: Troy Chang





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號碼(No.): CE/2015/93571B

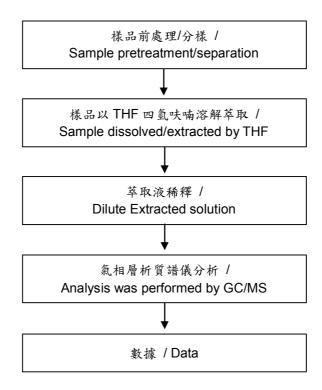
#### 可塑劑分析流程圖 / Analytical flow chart of phthalate content

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- 測試人員:徐毓明 / Name of the person who made measurement: Andy Shu
- 測試負責人:張啟興 / Name of the person in charge of measurement: Troy Chang

#### 【測試方法/Test method: IEC 62321-8】





# **Test Report**

美麗微半導體股份有限公司 FORMOSA MICROSEMI CO., LTD. 新北市土城區中央路三段208號5樓

5F., NO. 208, SEC. 3, ZHONGYANG RD., TUCHENG DIST., NEW TAIPEI CITY 23680, TAIWAN

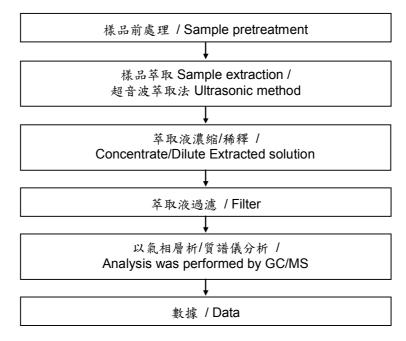
號碼(No.): CE/2015/93571B

### 六溴環十二烷分析流程圖 / HBCDD analytical flow chart

日期(Date): 2015/09/24

頁數(Page): 13 of 16

- 測試人員: 翁賜彬 / Name of the person who made measurement: Roman Wong
- 測試負責人:張啟興 / Name of the person in charge of measurement: Troy Chang





# **Test Report**

美麗微半導體股份有限公司 FORMOSA MICROSEMI CO., LTD. 新北市土城區中央路三段208號5樓

5F., NO. 208, SEC. 3, ZHONGYANG RD., TUCHENG DIST., NEW TAIPEI CITY 23680, TAIWAN

號碼(No.): CE/2015/93571B

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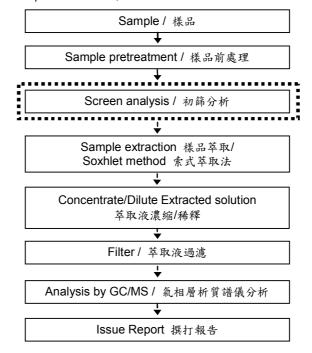
#### 多溴聯苯/多溴聯苯醚分析流程圖 / PBB/PBDE analytical FLOW CHART

日期(Date): 2015/09/24

- 測試人員: 翁賜彬 / Name of the person who made measurement: Roman Wong
- 測試負責人: 張啟興 / Name of the person in charge of measurement: Troy Chang

初次測試程序 / First testing process -選擇性篩檢程序 / Optional screen process ••••••

確認程序 / Confirmation process - - - - - ▶





# **Test Report**

美麗微半導體股份有限公司 FORMOSA MICROSEMI CO., LTD. 新北市土城區中央路三段208號5樓

5F., NO. 208, SEC. 3, ZHONGYANG RD., TUCHENG DIST., NEW TAIPEI CITY 23680, TAIWAN

號碼(No.): CE/2015/93571B

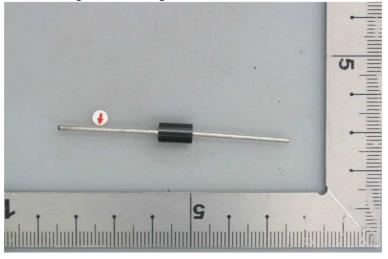
\* 照片中如有箭頭標示,則表示為實際檢測之樣品/部位. \* (The tested sample / part is marked by an arrow if it's shown on the photo.)

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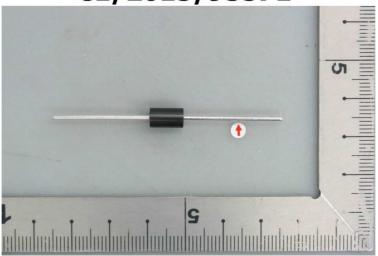
測試部位(PART NAME)No.1

CE/2015/90390 NO.1



測試部位(PART NAME)No. 2

CE/2015/93571





# **Test Report**

美麗微半導體股份有限公司 FORMOSA MICROSEMI CO., LTD. 新北市土城區中央路三段208號5樓 5F., NO. 208, SEC. 3, ZHONGYANG RD., TUCHENG DIST., NEW TAIPEI CITY 23680, TAIWAN

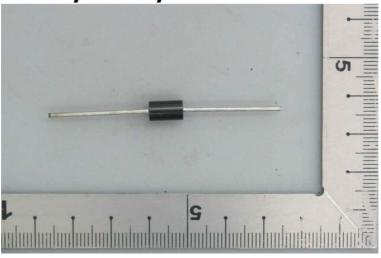
號碼(No.): CE/2015/93571B

測試部位(PART NAME)No.3

CE/2015/90390

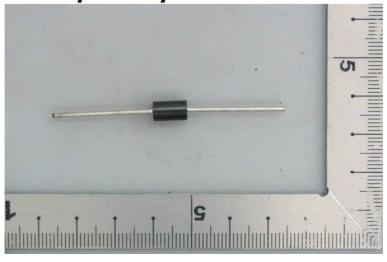
日期(Date): 2015/09/24

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測試部位(PART NAME)No.4

CE/2015/90390 NO.3



\*\* 報告結尾 (End of Report) \*\*